

L Number	Hits	Search Text	DB	Time stamp
1	30156	(single near crystal\$4) near3 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/30 15:34
2	13563	((single near crystal\$4) near3 substrate) and (opening or vias or cavity or trench or groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/30 15:37
3	4408	((single near crystal\$4) near3 substrate) and (opening or vias or cavity or trench or groove)) and isolation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/30 15:37
4	866	relaxed same defect\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/30 15:39
5	260	(relaxed same defect\$1) and strained	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/30 15:39
6	189	((relaxed same defect\$1) and strained) and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/30 15:39
7	92	((single near crystal\$4) near3 substrate) and (opening or vias or cavity or trench or groove)) and (relaxed same defect\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/30 15:40
8	51	((single near crystal\$4) near3 substrate) and (opening or vias or cavity or trench or groove)) and (relaxed same defect\$1)) and strained	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/30 15:40